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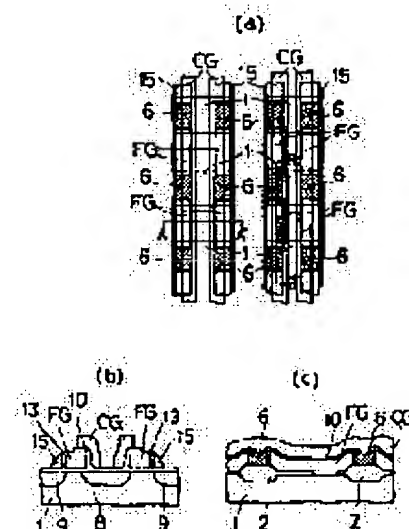
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(54) ELECTRICALLY ERASABLE NON-VOLATILE SEMICONDUCTOR MEMORY DEVICE AND MANUFACTURE THEREOF

(57)Abstract:

PURPOSE: To embody further reduction and higher integration by reducing an erase gate occupancy area of an electrically erasable non-volatile semiconductor memory device (EEPROM) which is provided with a floating gate, a control gate, and an erase gate on an MOS type transistor device.

CONSTITUTION: The sides of a floating gate FG are coated with an erasable insulation film 13, thereby forming a control gate CG and further forming an erase gate 15 on the side of the FG in a self-matching manner by way of the erasable insulation film 13. Since the erase gate is formed on the side of the floating gate, it is possible to reduce an occupancy area.



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